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	APPLICANT: Hans Joachim Müssig	
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UNITED STATES PATENT DOCUMENTS

EXAM. INITIAL		DOCUMENT NUMBER	ISSUE/PUBL DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>MDH</i>	US	2002/0036313	3-28-2002	Sam Yang et al.			
	US	2003/0228747	12-11-2003	Kie Y. Ahn et al.			
	US	6,656,852	12-2-2003	Antonio Luis Pacheco Rotondaro et al.			
	US	2003/0119291	6-26-2003	Kie Y. Ahn			
	US	5,356,833	10-18-1994	Papu D. Maniar et al.			
<i>↓</i>	US	2003/0193061	10-16-2003	Hans-Jörg Osten			

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	INVENTOR/ASSIGNEE	CLASS	SUBCLASS	TRANSLATION YES/NO
<i>MDH</i>	WO	02/097895	12-5-2002	Dietmar Krüger et al.			abstract only

OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)

<i>MDH</i>	Surface Science 504 (2002) 159-166, XP-001189099, Initial stages of praseodymium oxide film formation on Si(001), H.-J. Müssig et al., IHP, Im Technologiepark 25, D-15236 Frankfurt (Oder), Germany; received 8 September 2001, accepted for publication 3 Dec. 2001.
<i>MDH</i>	2001 IRW Final Report, 0-7803-7167-4/01/2001 IEEE, Can Praseodymium Oxide be an Alternative High-K Gate Dielectric Material for Silicon Integrated Circuits?, H. -J Müssig et al., IHP, Im Technologiepark 25, D-15236 Frankfurt (Oder), Germany.

Examiner *Mona D. Hanson*Date: *August 24, 2005*